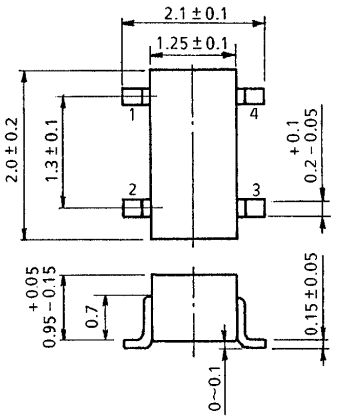
TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC5093

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

- Low Noise Figure, High Gain.
- NF = 1.8dB, $|S_{21e}|^2$ = 9.5dB (f = 2GHz)

Unit in mm



1, 3. EMITTER
2. BASE
4. COLLECTOR

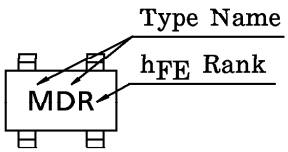
USQ	
JEDEC	—
EIAJ	—
TOSHIBA	2-2K1A

Weight : 0.006g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	10	V
Emitter-Base Voltage	V_{EBO}	1.5	V
Base Current	I_B	20	mA
Collector Current	I_C	40	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

MARKING



MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	f_T	V_{CE} = 8V, I_C = 20mA	7	10	—	GHz
Insertion Gain	$\|S_{21e}\|^2$ (1)	V_{CE} = 8V, I_C = 20mA, f = 1GHz	12	15	—	dB
	$\|S_{21e}\|^2$ (2)	V_{CE} = 8V, I_C = 20mA, f = 2GHz	6.5	9.5	—	
Noise Figure	NF (1)	V_{CE} = 8V, I_C = 5mA, f = 1GHz	—	1.4	2.5	dB
	NF (2)	V_{CE} = 8V, I_C = 5mA, f = 2GHz	—	1.8	3	

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = 10V, I_E = 0	—	—	1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 1V, I_C = 0	—	—	1	μA
DC Current Gain	h_{FE} (Note 1)	V_{CE} = 8V, I_C = 20mA	50	—	160	—
Output Capacitance	C_{ob}	V_{CB} = 5V, I_E = 0, f = 1MHz (Note 2)	—	0.65	1.05	pF
Reverse Transfer Capacitance	C_{re}		—	0.45	0.95	pF

(Note 1) : h_{FE} Classification R : 50~100, O : 80~160

(Note 2) : C_{re} is measured by 3 terminal method with capacitance bridge.

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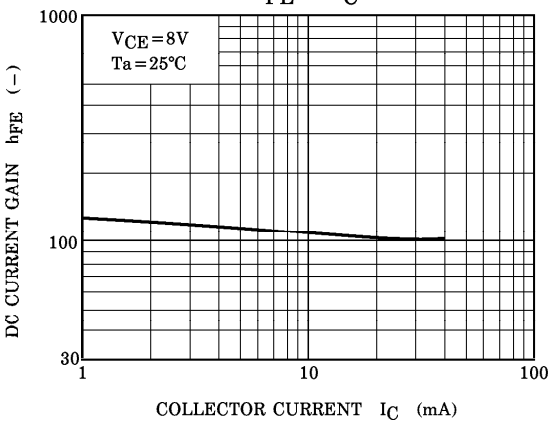
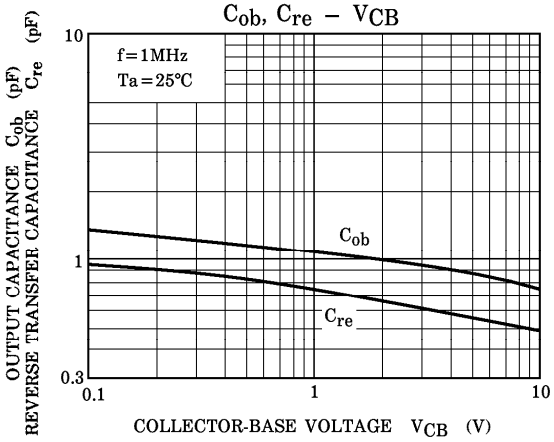
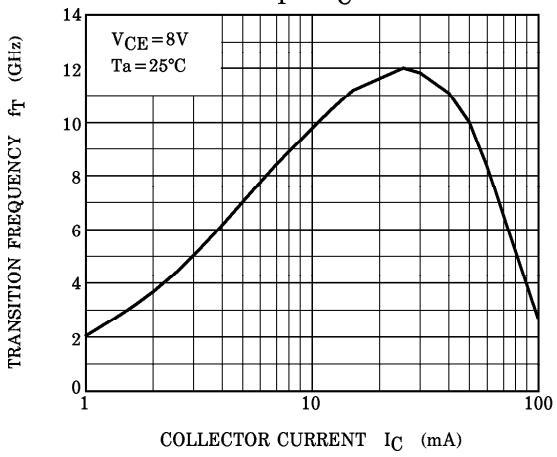
h_{FE} – I_C



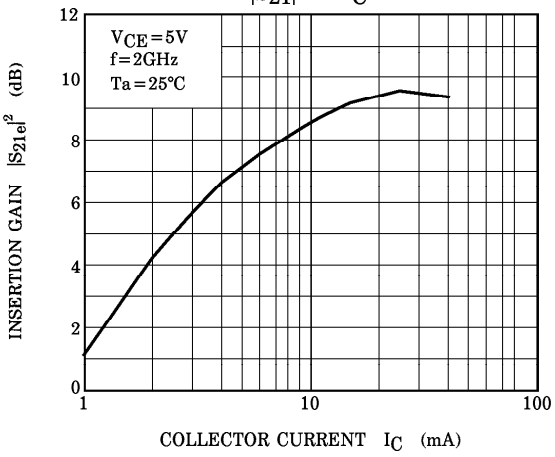
C_{ob}, C_{re} – V_{CB}



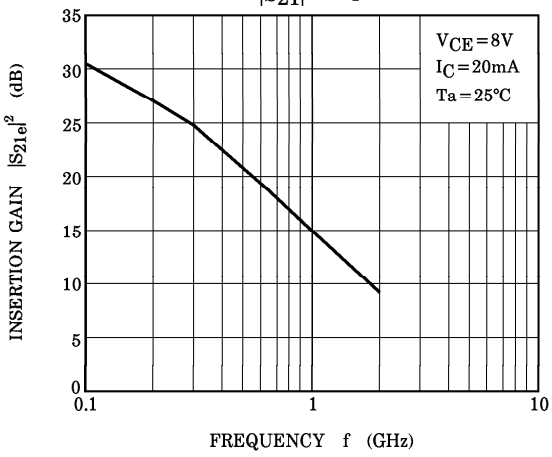
f_T – I_C



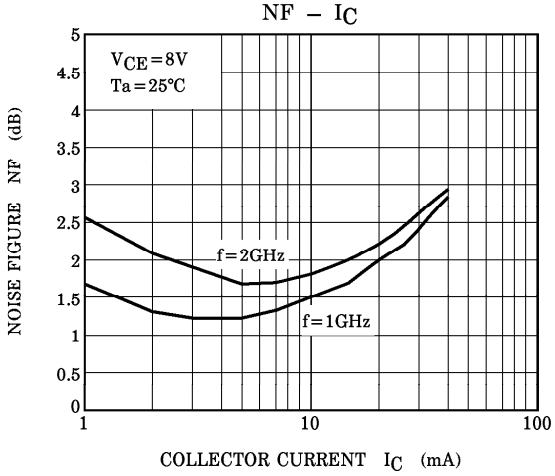
$|S_{21}|^2$ – I_C



$|S_{21}|^2$ – f



NF – I_C



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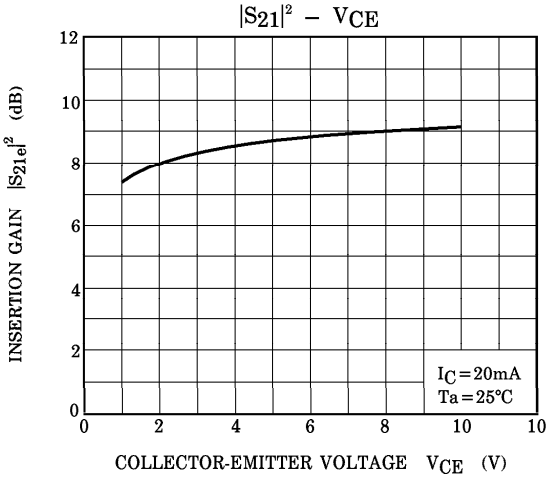
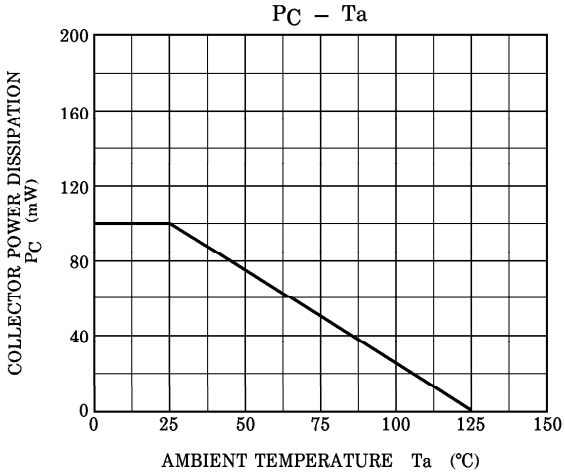




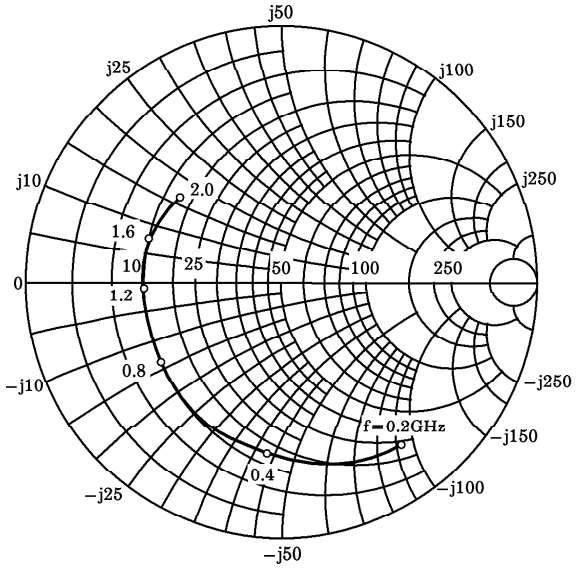
S-Parameter $Z_O = 50\Omega$, Ta = 25°C
V_{CE} = 8V, I_C = 5mA

frequency	S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.801	−54.4	12.628	145.4	0.047	63.2	0.864	−32.2
400	0.696	−95.6	9.664	121.9	0.072	48.8	0.675	−54.2
600	0.617	−124.7	7.307	106.2	0.083	42.3	0.543	−68.4
800	0.585	−146.3	5.779	95.1	0.090	39.3	0.456	−79.6
1000	0.554	−163.0	4.674	86.8	0.095	39.5	0.400	−88.6
1200	0.545	−176.5	3.902	80.0	0.099	40.4	0.357	−96.8
1400	0.529	171.3	3.350	75.0	0.103	42.5	0.323	−104.5
1600	0.529	161.1	2.929	70.0	0.108	44.8	0.299	−111.0
1800	0.527	150.4	2.612	66.1	0.116	47.1	0.277	−116.5
2000	0.513	141.0	2.366	62.1	0.122	49.6	0.258	−120.3

V_{CE} = 8V, I_C = 20mA

frequency	S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.556	−95.4	23.034	126.0	0.032	55.7	0.629	−53.5
400	0.521	−137.0	13.888	105.1	0.045	52.0	0.407	−75.8
600	0.505	−160.0	9.597	94.2	0.054	54.0	0.311	−89.3
800	0.505	−174.7	7.272	86.8	0.064	56.4	0.263	−101.3
1000	0.508	172.6	5.797	81.0	0.075	59.0	0.233	−112.0
1200	0.519	163.1	4.800	76.5	0.085	60.4	0.208	−122.9
1400	0.518	153.4	4.119	72.8	0.095	62.0	0.189	−132.7
1600	0.525	144.3	3.603	69.1	0.106	63.2	0.172	−141.7
1800	0.532	135.6	3.231	66.4	0.119	63.8	0.153	−149.3
2000	0.523	125.9	2.952	62.8	0.131	64.6	0.131	−153.9

S_{11e}
V_{CE} = 8V
I_C = 5mA
Ta = 25°C
(Unit : Ω)



S_{21e}
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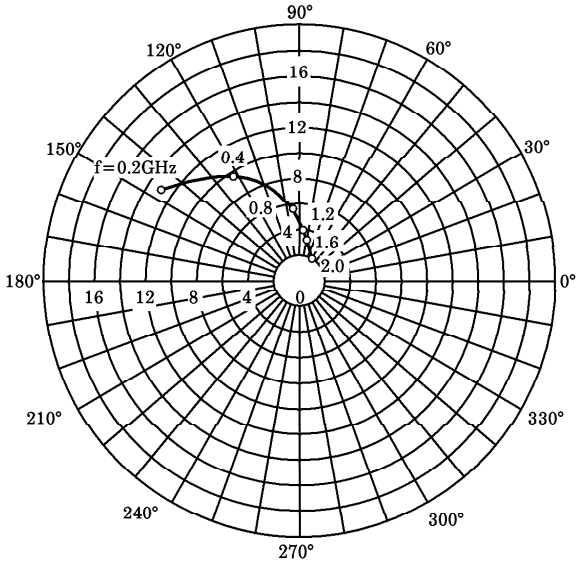
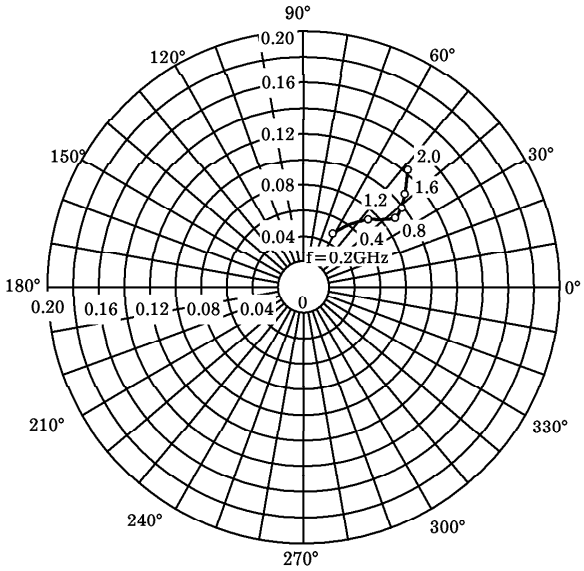


S_{12e}
V_{CE} = 8V
I_C = 5mA
Ta = 25°C



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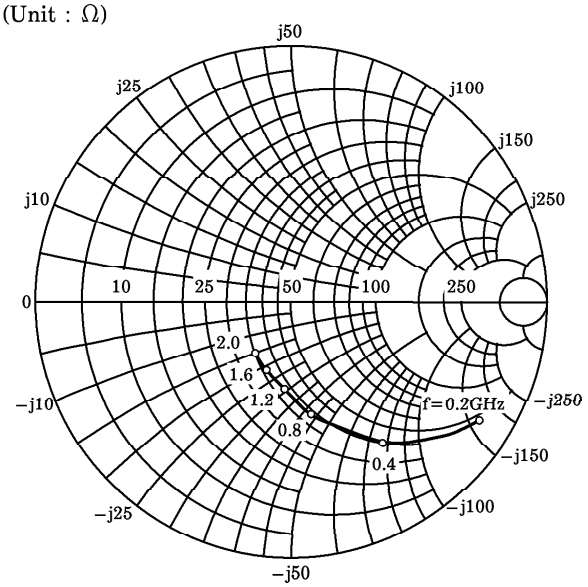

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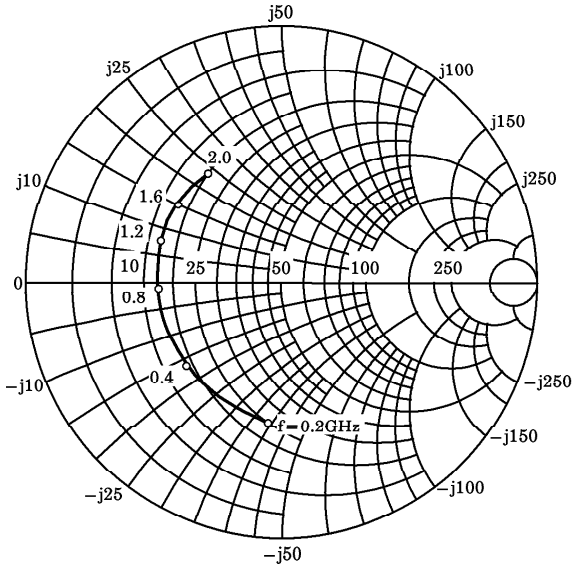

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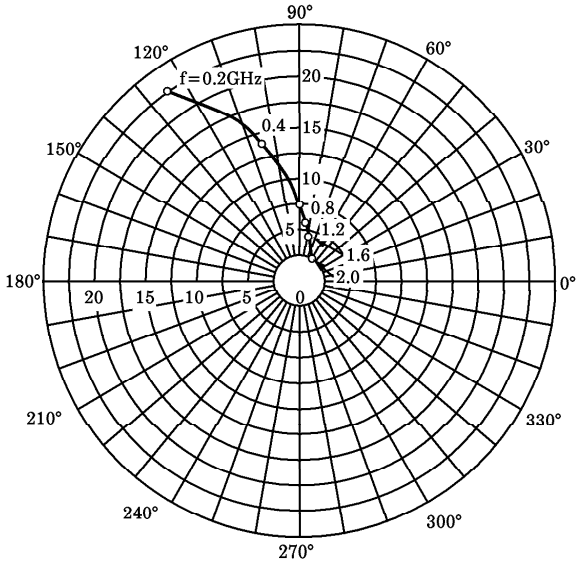

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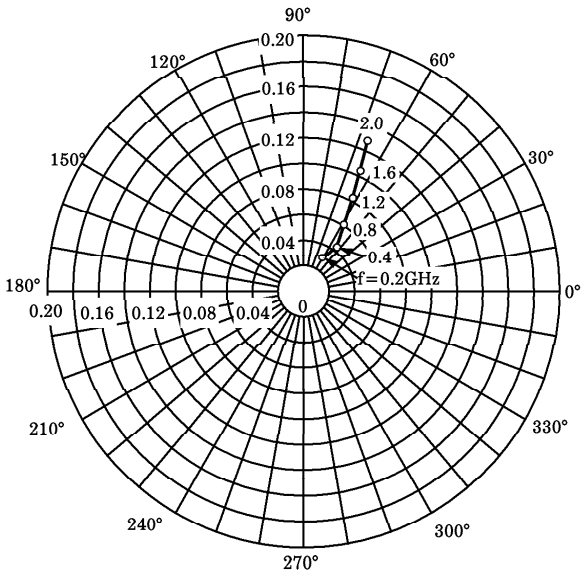

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